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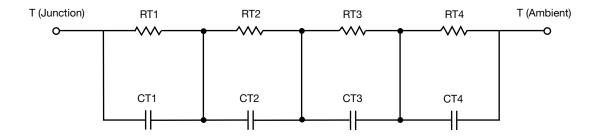
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RT1	N/A	341.8649m	N/A			
RT2	N/A	401.2509m	N/A			
RT3	N/A	239.8259m	N/A			
RT4	N/A	9.1706m	N/A			
	THERMAL CAPAC	CITANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CT1	N/A	495.7458u	N/A			
CT2	N/A	34.1921m	N/A			
CT3	N/A	19.0551m	N/A			
CT4	N/A	1.6169	N/A			

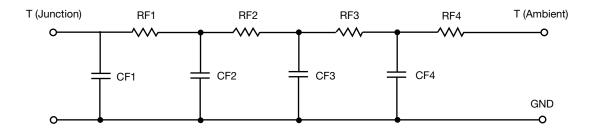
Note

• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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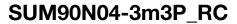
R-C THERMAL MODEL FOR FILTER CONFIGURATION



R-C VALUES FOR FILTER CONFIGURATION						
THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RF1	N/A	380.9529m	N/A			
RF2	N/A	350.6341m	N/A			
RF3	N/A	233.0475m	N/A			
RF4	N/A	36.8594m	N/A			
	THERMAL CAPAC	CITANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CF1	N/A	509.6655u	N/A			
CF2	N/A	12.4656m	N/A			
CF3	N/A	14.9616m	N/A			
CF4	N/A	1.6204	N/A			

Note

• n/a indicates not applicable





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